

## Tandem 600 V hyperfast boost diode

**Table 1. Main product characteristics**

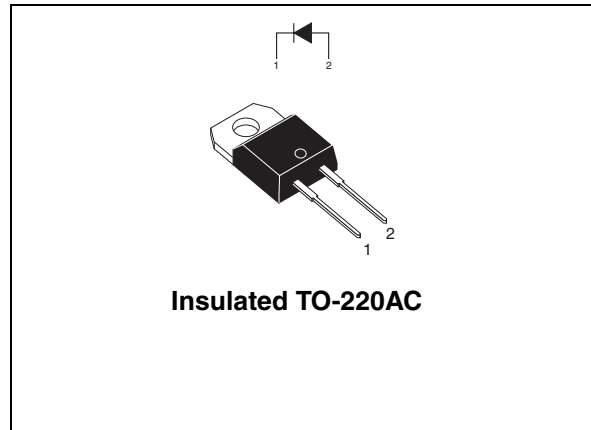
$I_{F(AV)}$	8 A
$V_{RRM}$	600 V
$T_j(max)$	150° C
$V_F(max)$	2.24 V
$I_{RM}(typ.)$	4 A
$t_{rr}(typ.)$	13 ns

### Features and benefits

- Especially suited as boost diode in continuous mode power factor correctors and hard switching conditions
- Designed for high di/dt operation. Hyperfast recovery current to compete with SiC devices. Allows downsizing of mosfet and heatsinks
- Internal ceramic insulated devices with equal thermal conditions for both 300 V diodes
- Insulation (2500 V<sub>RMS</sub>) allows placement on same heatsink as mosfet and flexible heatsinking on common or separate heatsink
- Static and dynamic equilibrium of internal diodes are warranted by design
- Package Capacitance: C = 7 pF

**Table 3. Absolute ratings (limiting values)**

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	600	V
$I_{F(RMS)}$	RMS forward voltage	14	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	180 A
$T_{stg}$	Storage temperature range	-65 to + 150	° C
$T_j$	Maximum operating junction temperature	150	° C



### Description

The TURBOSWITCH “H” is an ultra high performance diode composed of two 300 V dice in series. TURBOSWITCH “H” family drastically cuts losses in the associated MOSFET when run at high di<sub>F</sub>/dt.

**Table 2. Order codes**

Part number	Marking
STTH806DTI	STTH806DTI

# 1 Characteristics

**Table 4. Thermal parameter**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case thermal resistance	2.6	°C/W

**Table 5. Static electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ C$	$V_R = V_{RRM}$		10	$\mu A$
		$T_j = 125^\circ C$		15	100	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ C$	$I_F = 8 A$		3.6	V
		$T_j = 150^\circ C$		1.95	2.4	

1. Pulse test:  $t_p = 100 \text{ ms}$ ,  $\delta < 2\%$
2. Pulse test:  $t_p = 380 \text{ }\mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:  
 $P = 1.7 \times I_{F(AV)} + 0.087 I_{F(RMS)}^2$

**Table 6. Dynamic characteristics**

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit	
$t_{rr}$	Reverse recovery time	$T_j = 25^\circ C$	$I_F = 0.5 A, I_{rr} = 0.25 A, I_R = 1 A$		13	ns	
			$I_F = 1 A, di_F/dt = - 50 A/\mu s$ $V_R = 30 V$				30
$I_{RM}$	Reverse recovery current	$T_j = 125^\circ C$	$I_F = 8 A, V_R = 400,$ $V di_F/dt = - 200 A/\mu s$		4	5.5	A
S	Reverse recovery softness factor				0.4		
$Q_{rr}$	Reverse recovery charges				50		

**Table 7. Turn-on switching characteristics**

Symbol	Parameter	Test conditions	Min.	Typ	Max.	Unit
$t_{fr}$	Forward recovery time	$T_j = 25^\circ C$			200	ns
$V_{FP}$	Forward recovery voltage	$T_j = 25^\circ C$			7	V

Figure 1. Conduction losses versus average current

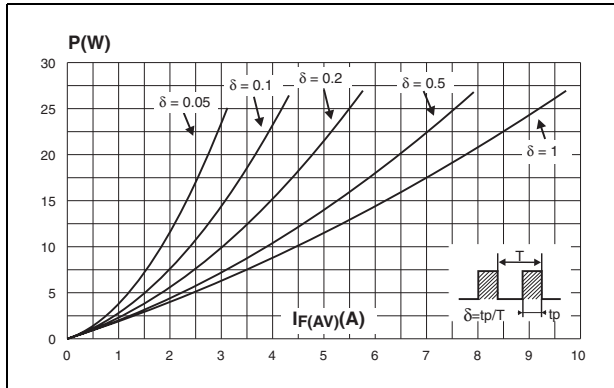


Figure 2. Forward voltage drop versus forward current

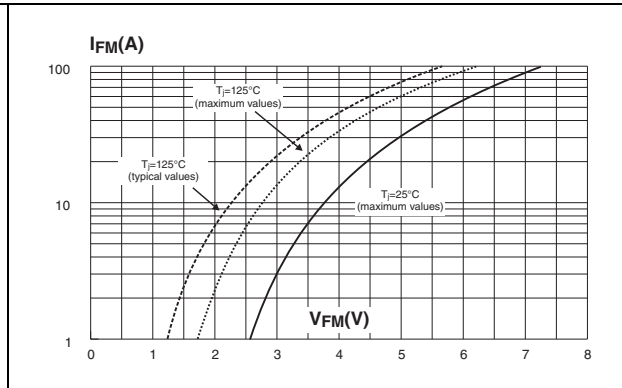


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

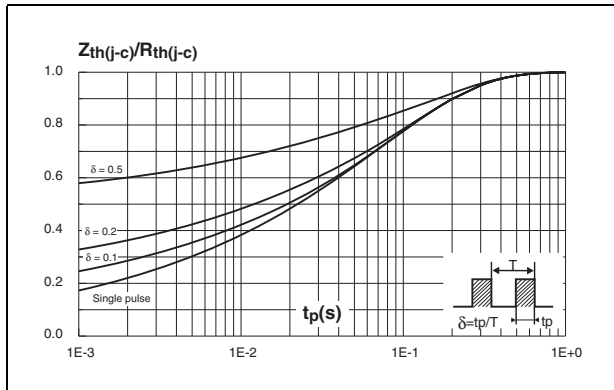


Figure 4. Peak reverse recovery current versus di\_F/dt (typical values)

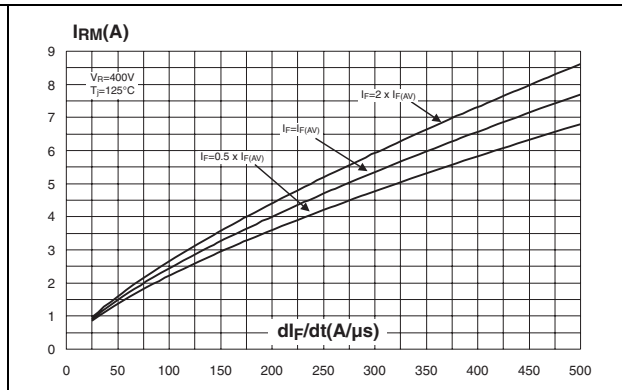


Figure 5. Reverse recovery time versus di\_F/dt (typical values)

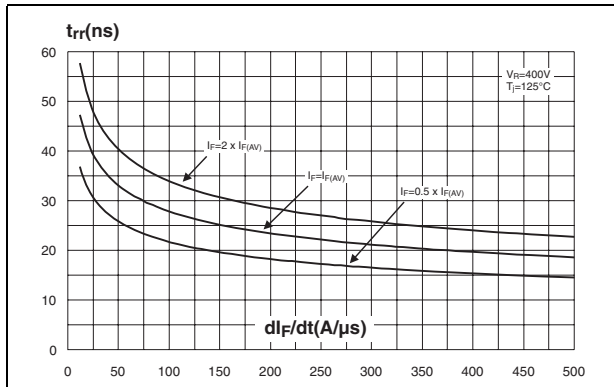


Figure 6. Reverse charges versus di\_F/dt (typical values)

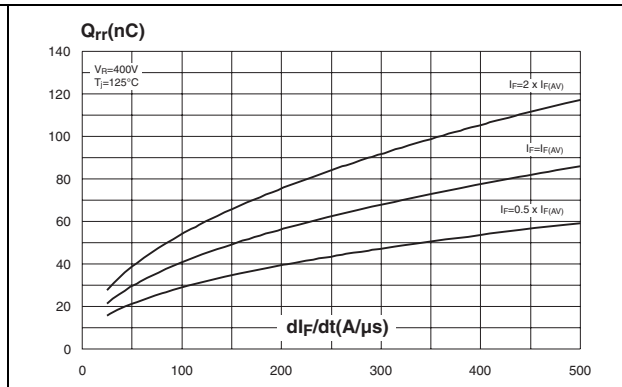


Figure 7. Softness factor versus  $di_F/dt$  (typical values)

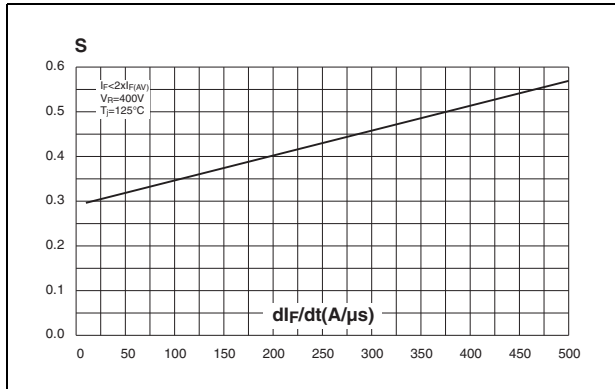


Figure 8. Relative variation of dynamic parameters versus junction temperature (reference:  $T_J = 125^\circ C$ )

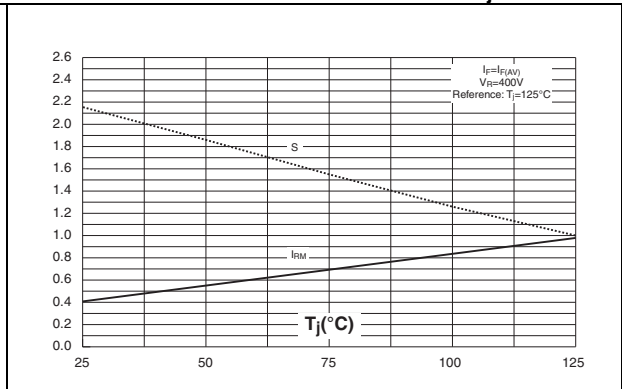


Figure 9. Transient peak forward voltage versus  $di_F/dt$  (typical values)

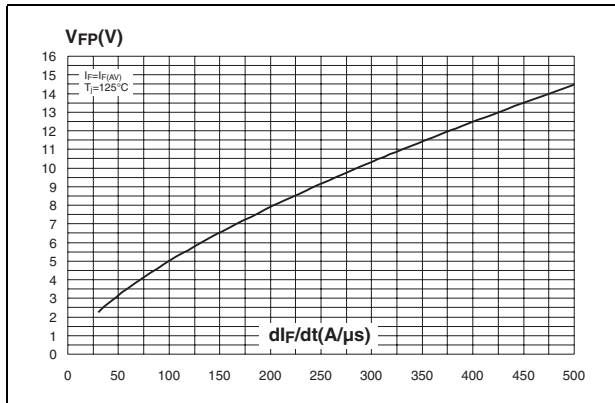
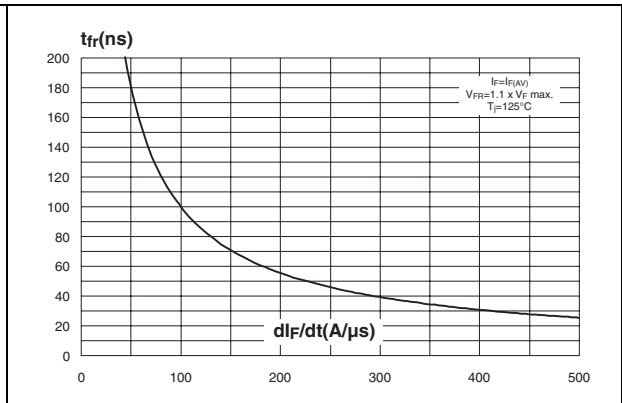


Figure 10. Forward recovery time versus  $di_F/dt$  (typical values)



## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: C
- Recommended torque value: 0.4 to 0.6 Nm

**Table 8. TO-220AC insulated dimensions**

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	4.80		5.40	0.189		0.212
F	6.20		6.60	0.244		0.259
ØI	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
M		2.60			0.102	

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com).

### 3 Ordering information

Table 9. Ordering information

Part number	Marking	Package	Weight	Base qty	Delivery mode
STTH806DTI	STTH806DTI	TO-220AC	2.3 g	50	Tube

### 4 Revision history

Table 10. Revision history

Date	Revision	Changes
Oct-2003	2A	Initial release
May-2004	3	Reformatted
29-Jun-2005	4	Corrections to typographical errors. No technical changes.
11-Jul-2007	5	Reformatted to current standards. Removed I <sub>PEAK</sub> parameter from <a href="#">Table 3: Absolute ratings (limiting values)</a> .

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